

The 21st Korean Conference on Semiconductors
제21회 한국반도체학술대회
February 24–26, 2014 / Hanyang University, Seoul, Korea

E. Compound Semiconductors 분과

[WF1-E] Compound Semiconductor I

Date	Feb. 26, 2014 (Wed.)
Place	Room F / 제1공학관 404호 (# 404, Engineering Building I)

Session Chair: 문재경 박사(ETRI), 차호영 교수(홍익대학교)

- WF1-E-1 10:50-11:05 Fast Recovery Diode Embedded Normally-off AlGaIn/GaN MOSHFET**
저자: 박봉렬, 이정연, 이재길, 한상우, 차호영
소속: 홍익대학교
- WF1-E-2 11:05-11:20 Home Appliance용 전력소자의 스위칭 항복 전압 향상을 위한 p-GaN Gate HFET의 Gate 특성 연구**
저자: 송미선, 김웅선, 신종훈, 장태훈
소속: LG전자 System, IC 연구소 IGBT Part
- WF1-E-3 11:20-11:35 Home Appliance용 AlGaIn/GaN HFET의 Au-Free 공정 적용에 대한 연구**
저자: 조영제, 고화영, 박진홍, 이호중, 장태훈
소속: IGBT Part, System IC R&D, LG Electronics
- WF1-E-4 11:35-11:50 Role of Thin Al₂O₃ Dielectric Layer in AlGaIn/GaN-Based MISHFET as Gate Insulator and Surface Protection Layer during RTP**
저자: V. Sindhuri, Do-Kywn Kim, Dong-Seok Kim, Chul-Ho Won, Jun-Hyeok Lee, and Jung-Hee Lee
소속: School of Electronics Engineering, Kyungpook National University
- WF1-E-5 11:50-12:05 Large GaN-SBD with a Symmetric Electrode Structure using an Ohmic Recess Process and Si Ohmic Metal**
저자: W.Y. Jang^{1,2}, H.G. Jang^{1,5}, J.H. Na¹, S.C. Ko¹, Y.R. Park¹, J.J. Kim^{1,3}, W.J. Jang¹, S.B. Bae¹, C.H. Jun¹, S.H. Moon¹, D.K. Kim², J.K. Mun¹, H.M. Park⁴, and E.S. Nam¹
소속: ¹Electronics and Telecommunications Research Institute, ²Sejong University, ³Chunbuk National University, ⁴Dongguk University, ⁵University of Science and Technology